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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 504K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1156-BBGA, FCBGA
Supplier Device Package	1156-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu7cg-1ffvc1156e

Table 1: Absolute Maximum Ratings⁽¹⁾ (Cont'd)

Symbol	Description	Min	Max	Units
Video Codec Unit				
V _{CCINT_VCU}	Internal supply voltage for the video codec unit.	-0.500	1.000	V
PL System Monitor				
V _{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V _{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T _{STG}	Storage temperature (ambient).	-65	150	°C
T _{SOL}	Maximum soldering temperature. ⁽¹²⁾	-	260	°C
T _j	Maximum junction temperature. ⁽¹²⁾	-	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to [Table 6](#), [Table 7](#), and [Table 8](#) for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* ([UG571](#)).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) or *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* ([UG1075](#)).

Recommended Operating Conditions

 Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC_PSINTFP}$ ⁽³⁾	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC_PSINTFP_DDR}$ ⁽³⁾	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR} ⁽⁴⁾	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC_PSDDR_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO} ⁽⁵⁾	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	$V_{CCO_PSIO} + 0.200$	V
	PS DDR I/O input voltage.	–0.200	–	$V_{CCO_PSDDR} + 0.200$	
V_{CC_PSBATT} ⁽⁶⁾	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO} ⁽⁷⁾	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: Power-on Current by Device⁽¹⁾

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}^+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
$I_{CCINT_IOMIN}^+$ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}^+$ $I_{CCINT_IOQ}^+$	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}^+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}^+$ I_{CCAUX_IOMIN}	I_{CCAUXQ}^+ $I_{CCAUX_IOQ}^+$	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: Power Supply Ramp Time

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT} .	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO} .	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU} .	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO} .	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX} .	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM} .	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC_PSINTFP}$	Ramp time from GND to 95% of $V_{CC_PSINTFP}$.	0.2	40	ms
$T_{VCC_PSINTLP}$	Ramp time from GND to 95% of $V_{CC_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX} .	0.2	40	ms
$T_{VCC_PSINTFP_DDR}$	Ramp time from GND to 95% of $V_{CC_PSINTFP_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC} .	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL} .	0.2	40	ms
$T_{PS_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC_MGTRAVCC}$.	0.2	40	ms
$T_{PS_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC_MGTRAVTT}$.	0.2	40	ms

Table 17: Differential SelectIO DC Input and Output Levels

I/O Standard	V _{ICM} (V) ⁽¹⁾			V _{ID} (V) ⁽²⁾			V _{ILHS} ⁽³⁾	V _{IHHS} ⁽³⁾	V _{OCM} (V) ⁽⁴⁾			V _{OD} (V) ⁽⁵⁾		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS ⁽⁸⁾	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
LVPECL	0.300	1.200	1.425	0.100	0.350	0.600	–	–	–	–	–	–	–	–
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
SLVS_400_25	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS ⁽⁹⁾	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage (Q – \bar{Q}).
- V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
- V_{OCM} is the output common mode voltage.
- V_{OD} is the output differential voltage (Q – \bar{Q}).
- LVDS_25 is specified in Table 23.
- LVDS is specified in Table 24.
- Only the SUB_LVDS receiver is supported in HD I/O banks.
- High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 18: Complementary Differential SelectIO DC Input and Output Levels for HD I/O Banks

I/O Standard	V _{ICM} (V) ⁽¹⁾			V _{ID} (V) ⁽²⁾		V _{OL} (V) ⁽³⁾	V _{OH} (V) ⁽⁴⁾	I _{OL}	I _{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V _{CCO} – 0.400	8.0	–8.0
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V _{CCO} – 0.400	8.0	–8.0
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V _{CCO}	80% V _{CCO}	0.1	–0.1
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	8.9	–8.9
DIFF_SSTL135_II	0.300	0.675	1.000	0.100	–	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	13.0	–13.0
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	8.9	–8.9
DIFF_SSTL15_II	0.300	0.750	1.125	0.100	–	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	13.0	–13.0
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V _{CCO} /2) – 0.470	(V _{CCO} /2) + 0.470	8.0	–8.0
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V _{CCO} /2) – 0.600	(V _{CCO} /2) + 0.600	13.4	–13.4

Notes:

- V_{ICM} is the input common mode voltage.
- V_{ID} is the input differential voltage.
- V_{OL} is the single-ended low-output voltage.
- V_{OH} is the single-ended high-output voltage.

Table 26: Speed Grade Designations by Device (Cont'd)

Device	Speed Grade, Temperature Ranges, and V _{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU5EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU5EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU6CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU6EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU7CG	-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU9CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU9EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)

PS Configuration

Table 39: Processor Configuration Access Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz

Table 40: Boundary-Scan Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max

Notes:

- The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength.

Table 42: Linear Quad-SPI Interface⁽¹⁾

Symbol	Description	Load Conditions ⁽²⁾	Min	Max	Units
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK5}	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
T _{QSPISSCLK5}	Slave select asserted to next clock edge. ⁽³⁾	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPISCLKSS5}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPICKO5}	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
T _{QSPIDCK5}	Setup time, all inputs.	15 pF	2.4	–	ns
		30 pF	2.4	–	ns
T _{QSPICKD5}	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
F _{QSPIREFCLK5}	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz
F _{QSPICLK5}	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz

Notes:

1. The test conditions are configured for the linear Quad-SPI interface at 100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for stacked modes.
3. T_{QSPISSCLK5} is only valid when two reference clock cycles are programmed between chip select and clock.

PS USB Interface

 Table 43: ULPI Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{ULPIDCK}	Input setup to ULPI clock, all inputs.	4.5	–	ns
T _{ULPICKD}	Input hold to ULPI clock, all inputs.	0	–	ns
T _{ULPICKO}	ULPI clock to output valid, all outputs.	2.0	8.86	ns
F _{ULPICLK}	ULPI reference clock frequency.	–	60	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS Gigabit Ethernet Controller Interface

 Table 44: RGMII Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{DCGEMTXCLK}	Transmit clock duty cycle.	45	55	%
T _{GEMTXCKO}	TXD output clock to out time.	-0.5	0.5	ns
T _{GEMRXDCK}	RXD input setup time.	0.8	-	ns
T _{GEMRXCKD}	RXD input hold time.	0.8	-	ns
T _{MDIOCLK}	MDC output clock period.	400	-	ns
T _{MDIOCKL}	MDC low time.	160	-	ns
T _{MDIOCKH}	MDC high time.	160	-	ns
T _{MDIODCK}	MDIO input data setup time.	80	-	ns
T _{MDIOCKD}	MDIO input data hold time.	0.0	-	ns
T _{MDIOCKO}	MDIO output data delay time.	-1.0	15	ns
F _{GETXCLK}	RGMII_TX_CLK transmit clock frequency.	-	125	MHz
F _{GERXCLK}	RGMII_RX_CLK receive clock frequency.	-	125	MHz
F _{ENET_REF_CLK}	Ethernet reference clock frequency.	-	125	MHz

Notes:

1. The test conditions are configured to the LVCMOS 2.5V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SD/SDIO Controller Interface

 Table 45: SD/SDIO Interface⁽¹⁾

Symbol	Description	Min	Max	Units
SD/SDIO Interface DDR50 Mode				
T _{DCDDRCLK}	SD device clock duty cycle.	45	55	%
T _{SDDDRCKO1}	Clock to output delay, data. ⁽²⁾	1.0	6.8	ns
T _{SDDRIVW}	Input valid data window. ⁽³⁾	3.5	-	ns
T _{SDDDRDCK2}	Input setup time, command.	4.7	-	ns
T _{SDDDRCKD2}	Input hold time, command.	1.5	-	ns
T _{SDDDRCKO2}	Clock to output delay, command.	1.0	13.8	ns
F _{SDDDRCLK}	High-speed mode SD device clock frequency.	-	50	MHz
SD/SDIO Interface SDR104				
T _{DCSDHCLK1}	SD device clock duty cycle.	40	60	%
T _{SDSDRCKO1}	Clock to output delay, all outputs. ⁽²⁾	1.0	3.2	ns
T _{SSDSR1IVW}	Input valid data window. ⁽³⁾	0.5	-	UI
F _{SDSDRCLK1}	SDR104 mode device clock frequency.	-	200	MHz
SD/SDIO Interface SDR50/25				
T _{DCSDHCLK2}	SD device clock duty cycle.	40	60	%
T _{SDSDRCKO2}	Clock to output delay, all outputs. ⁽²⁾	1.0	6.8	ns
T _{SSDSR2IVW}	Input valid data window. ⁽³⁾	0.3	-	UI

PS I2C Controller Interface

Table 47: I2C Interface⁽¹⁾

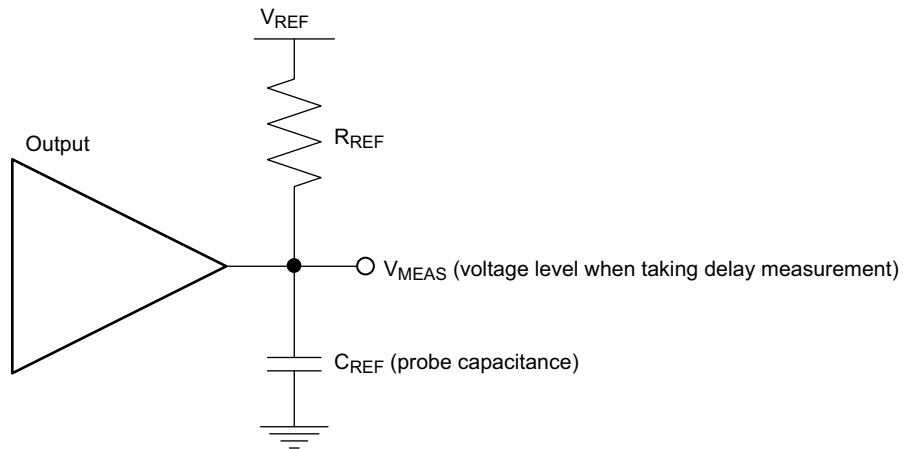
Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	μ s
$T_{I2CFCKH}$	SCL High time.	0.6	–	μ s
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	μ s
$T_{I2CSCKH}$	SCL High time.	4.0	–	μ s
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

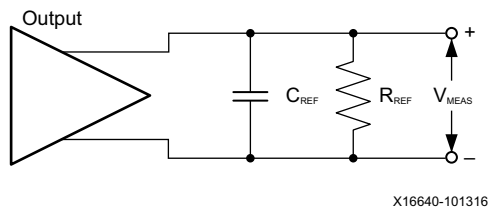
Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in [Figure 1](#) and [Figure 2](#).



X16654-101316

Figure 1: Single-Ended Test Setup



X16640-101316

Figure 2: Differential Test Setup

Parameters V_{REF} , R_{REF} , C_{REF} , and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from [Table 79](#).
2. Record the time to V_{MEAS} .
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS} .
5. Compare the results of [step 2](#) and [step 4](#). The increase or decrease in delay yields the actual propagation delay of the PCB trace.

UltraRAM Switching Characteristics

The *UltraScale Architecture and Product Overview* ([DS890](#)) lists the Zynq UltraScale+ MPSoC that include this memory.

Table 81: UltraRAM Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX}	UltraRAM maximum frequency with OREG_B = True.	650	600	575	500	481	MHz
F _{MAX_ECC}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = True.	450	400	386	325	315	MHz
F _{MAX_NORPIPELINE}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = False.	550	500	478	425	408	MHz
T _{PW} ⁽¹⁾	Minimum pulse width.	650	700	730	800	832	ps
T _{RSTPW}	Asynchronous reset minimum pulse width. One cycle required.	1 clock cycle					

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Input/Output Delay Switching Characteristics

Table 82: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{REFCLK}	REFCLK frequency for IDELAYCTRL (component mode).	300 to 800					MHz
	REFCLK frequency for BITSLICE_CONTROL (native mode). ⁽¹⁾	300 to 2666.67	300 to 2666.67	300 to 2400	300 to 2400	300 to 2133	MHz
T _{MINPER_CLK}	Minimum period for IODELAY clock.	3.195	3.195	3.195	3.195	3.195	ns
T _{MINPER_RST}	Minimum reset pulse width.	52.00					ns
T _{IDELAY_RESOLUTION} / T _{ODELAY_RESOLUTION}	IDELAY/ODELAY chain resolution.	2.1 to 12					ps

Notes:

1. PLL settings could restrict the minimum allowable data rate. For example, when using a PLL with CLKOUTPHY_MODE = VCO_HALF, the minimum frequency is PLL_FVCOMIN/2.

Table 85: MMCM Specification (Cont'd)

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F _{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.

Device Pin-to-Pin Input Parameter Guidelines

The pin-to-pin numbers in [Table 90](#) and [Table 91](#) are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 90: Global Clock Input Setup and Hold With 3.3V HD I/O without MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard. (1)(2)(3)									
T _{PSFD_ZU2}	Global clock input and input flip-flop (or latch) without MMCM.	Setup	XCZU2	N/A	2.27	2.37	2.55	2.64	ns
T _{PHFD_ZU2}		Hold			-0.36	-0.36	-0.14	-0.14	ns
T _{PSFD_ZU3}		Setup	XCZU3	N/A	2.27	2.37	2.55	2.64	ns
T _{PHFD_ZU3}		Hold			-0.36	-0.36	-0.14	-0.14	ns
T _{PSFD_ZU4}		Setup	XCZU4	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU4}		Hold		-0.28	-0.28	-0.28	-0.09	-0.09	ns
T _{PSFD_ZU5}		Setup	XCZU5	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU5}		Hold		-0.28	-0.28	-0.28	-0.09	-0.09	ns
T _{PSFD_ZU6}		Setup	XCZU6	0.96	1.79	1.86	1.93	2.02	ns
T _{PHFD_ZU6}		Hold		-0.05	-0.05	-0.05	0.27	0.42	ns
T _{PSFD_ZU7}		Setup	XCZU7	1.43	2.32	2.42	2.60	2.69	ns
T _{PHFD_ZU7}		Hold		-0.40	-0.40	-0.40	-0.21	-0.21	ns
T _{PSFD_ZU9}		Setup	XCZU9	0.96	1.79	1.86	1.93	2.02	ns
T _{PHFD_ZU9}		Hold		-0.05	-0.05	-0.05	0.27	0.42	ns
T _{PSFD_ZU11}		Setup	XCZU11	1.28	2.01	2.07	2.59	2.59	ns
T _{PHFD_ZU11}		Hold		-0.29	-0.29	-0.29	-0.09	0.19	ns
T _{PSFD_ZU15}		Setup	XCZU15	0.96	1.79	1.85	1.92	2.01	ns
T _{PHFD_ZU15}		Hold		-0.04	-0.04	-0.04	0.27	0.43	ns
T _{PSFD_ZU17}		Setup	XCZU17	1.41	2.29	2.38	2.57	2.65	ns
T _{PHFD_ZU17}		Hold		-0.38	-0.38	-0.38	-0.19	-0.19	ns
T _{PSFD_ZU19}	Setup	XCZU19	1.41	2.29	2.38	2.57	2.65	ns	
T _{PHFD_ZU19}	Hold		-0.38	-0.38	-0.38	-0.19	-0.19	ns	

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 91: Global Clock Input Setup and Hold With MMCM

Symbol	Description	Device	Speed Grade and V _{CCIINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard. (1)(2)(3)									
T _{PSMMCMCC_ZU2}	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU2}		Hold			-0.19	-0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU3}		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU3}		Hold			-0.19	-0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU4}		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU4}		Hold			-0.12	-0.12	-0.12	0.27	0.48
T _{PSMMCMCC_ZU5}		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU5}		Hold			-0.12	-0.12	-0.12	0.27	0.48
T _{PSMMCMCC_ZU6}		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU6}		Hold			-0.11	-0.11	-0.11	0.16	0.18
T _{PSMMCMCC_ZU7}		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
T _{PHMMCMCC_ZU7}		Hold			-0.14	-0.14	-0.14	0.37	0.38
T _{PSMMCMCC_ZU9}		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU9}		Hold			-0.11	-0.11	-0.11	0.16	0.18
T _{PSMMCMCC_ZU11}		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
T _{PHMMCMCC_ZU11}		Hold			-0.08	-0.08	0.04	0.35	0.74
T _{PSMMCMCC_ZU15}		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU15}		Hold			-0.10	-0.10	-0.10	0.17	0.19
T _{PSMMCMCC_ZU17}		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
T _{PHMMCMCC_ZU17}		Hold			-0.16	-0.16	-0.16	0.31	0.34
T _{PSMMCMCC_ZU19}	Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns	
T _{PHMMCMCC_ZU19}	Hold			-0.16	-0.16	-0.16	0.31	0.34	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 92: Sampling Window

Description	Speed Grade and V _{CCINT} Operating Voltages					Units
	0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	
T _{SAMP_BUF} ⁽¹⁾	510	610	610	610	610	ps
T _{SAMP_NATIVE_DPA}	100	100	125	125	150	ps
T _{SAMP_NATIVE_BISC}	60	60	85	85	110	ps

Notes:

1. This parameter indicates the total sampling error of the Zynq UltraScale+ MPSoC DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include: CLK0 MMCM jitter, MMCM accuracy (phase offset), and MMCM phase shift resolution. These measurements do not include package or clock tree skew.

Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for clock transmitter and receiver data-valid windows.

Table 93: Package Skew

Symbol	Description	Device	Package	Value	Units
PKGSKEW	Package Skew	XCZU2	SBVA484	105	ps
			SFVA625	108	ps
			SFVC784	93	ps
		XCZU3	SBVA484	105	ps
			SFVA625	108	ps
			SFVC784	93	ps
		XCZU4	SFVC784		ps
			FBVB900		ps
		XCZU5	SFVC784		ps
			FBVB900		ps
		XCZU6	FFVC900	119	ps
			FFVB1156	134	ps
		XCZU7	FBVB900	141	ps
			FFVC1156	175	ps
			FFVF1517	305	ps
		XCZU9	FFVC900	119	ps
			FFVB1156	134	ps
		XCZU11	FFVC1156		ps
			FFVB1517		ps
			FFVF1517		ps
			FFVC1760	215	ps
		XCZU15	FFVC900	118	ps
			FFVB1156	132	ps
		XCZU17	FFVB1517	221	ps
FFVC1760	226		ps		
FFVD1760	178		ps		
FFVE1924	174		ps		
XCZU19	FFVB1517	221	ps		
	FFVC1760	226	ps		
	FFVD1760	178	ps		
	FFVE1924	174	ps		

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.
2. Package delay information is available for these device/package combinations. This information can be used to deskew the package.

Table 115: GTY Transceiver Transmitter Switching Characteristics (Cont'd)

Symbol	Description	Condition	Min	Typ	Max	Units
T _{J3.20}	Total jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.20	UI
D _{J3.20}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J2.5}	Total jitter ⁽³⁾⁽⁴⁾	2.5 Gb/s ⁽⁶⁾	–	–	0.20	UI
D _{J2.5}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J1.25}	Total jitter ⁽³⁾⁽⁴⁾	1.25 Gb/s ⁽⁷⁾	–	–	0.15	UI
D _{J1.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.06	UI
T _{J500}	Total jitter ⁽³⁾⁽⁴⁾	500 Mb/s ⁽⁸⁾	–	–	0.10	UI
D _{J500}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.03	UI

Notes:

- Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTY Quad) at maximum line rate.
- Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- All jitter values are based on a bit-error ratio of 10⁻¹².
- CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 117: GTY Transceiver Protocol List (Cont'd)

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort	DP 1.2B CTS	1.62–5.4	Compliant ⁽³⁾
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625 - 12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	All rates	Compliant

Notes:

1. 25 dB loss at Nyquist without FEC.
2. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
3. This protocol requires external circuitry to achieve compliance.

Table 119: Maximum Performance for Interlaken 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s Protocol and Lane Logic Mode Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages										Units		
		0.90V		0.85V			0.72V							
		-3 ⁽¹⁾		-2 ⁽¹⁾		-1		-2		-1				
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	440.79		440.79			N/A		402.84		N/A			MHz
F _{TX_SERDES_CLK}	Transmit serializer/deserializer clock	440.79		440.79			N/A		402.84		N/A			MHz
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00			N/A		250.00		N/A			MHz
		Min ⁽²⁾	Max	Min ⁽²⁾	Max	Min	Max	Min ⁽²⁾	Max	Min	Max			
F _{CORE_CLK}	Interlaken core clock	412.50 ⁽³⁾	479.20	412.50 ⁽³⁾	479.20	N/A		412.50	429.69	N/A		MHz		
F _{LBUS_CLK}	Interlaken local bus clock	300.00 ⁽⁴⁾	349.52	300.00 ⁽⁴⁾	349.52	N/A		300.00	349.52	N/A		MHz		

Notes:

1. 6 x 28.21 mode is only supported in the -2 (V_{CCINT}=0.85V) and -3 (V_{CCINT}=0.90V) speed grades.
2. These are the minimum clock frequencies at the maximum lane performance.
3. The minimum value for CORE_CLK is 451.36 MHz for the 6 x 28.21 Gb/s protocol.
4. The minimum value for LBUS_CLK is 330.00 MHz for the 6 x 28.21 Gb/s protocol.

Table 120: Maximum Performance for Interlaken 12 x 25.78125 Gb/s Lane Logic Only Mode Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages						Units				
		0.90V		0.85V		0.72V						
		-3		-2		-1						
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	402.84		402.84		N/A		N/A		N/A		MHz
F _{TX_SERDES_CLK}	Transmit serializer/deserializer clock	402.84		402.84		N/A		N/A		N/A		MHz
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		N/A		N/A		N/A		MHz
F _{CORE_CLK}	Interlaken core clock	412.50		412.50		N/A		N/A		N/A		MHz
F _{LBUS_CLK}	Interlaken local bus clock	349.52		349.52		N/A		N/A		N/A		MHz

PL SYSMON I2C/PMBus Interfaces

Table 125: PL SYSMON I2C Fast Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	μ s
T_{SMFCKH}	SCL High time	0.6	–	μ s
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: PL SYSMON I2C Standard Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	μ s
T_{SMSCKH}	SCL High time	4.0	–	μ s
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.